Aday J Molina-Mendoza

List of Publications by Year
in descending order

14	1,529	687363 13	1058476 14
papers	citations	h-index	g-index

14	14	14	2948
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Low thermal conductivity in franckeite heterostructures. Nanoscale, 2022, 14, 2593-2598.	5.6	4
2	Ultrafast machine vision with 2D material neural network image sensors. Nature, 2020, 579, 62-66.	27.8	546
3	Nonvolatile Programmable WSe₂ Photodetector. Advanced Optical Materials, 2020, 8, 2000417.	7.3	16
4	Nanoscale Thermal Transport in 2D Nanostructures from Cryogenic to Room Temperature. Advanced Electronic Materials, 2019, 5, 1900331.	5.1	15
5	Electroluminescence from multi-particle exciton complexes in transition metal dichalcogenide semiconductors. Nature Communications, 2019, 10, 1709.	12.8	100
6	Atomically thin pâ€“n junctions based on two-dimensional materials. Chemical Society Reviews, 2018, 47, 3339-3358.	38.1	231
7	Gate tunable photovoltaic effect in MoS₂ vertical pâ€“n homostructures. Journal of Materials Chemistry C, 2017, 5, 854-861.	5.5	50
8	Micro-reflectance and transmittance spectroscopy: a versatile and powerful tool to characterize 2D materials. Journal Physics D: Applied Physics, 2017, 50, 074002.	2.8	125
9	Franckeite as a naturally occurring van der Waals heterostructure. Nature Communications, 2017, 8, 14409.	12.8	103
10	High Current Density Electrical Breakdown of TiS₃ Nanoribbonâ€Based Fieldâ€Effect Transistors. Advanced Functional Materials, 2017, 27, 1605647.	14.9	52
11	Electronics and optoelectronics of quasi-1D layered transition metal trichalcogenides. 2D Materials, 2017, 4, 022003.	4.4	146
12	Characterization of highly crystalline lead iodide nanosheets prepared by room-temperature solution processing. Nanotechnology, 2017, 28, 455703.	2.6	45
13	Engineering the optoelectronic properties of MoS₂ photodetectors through reversible noncovalent functionalization. Chemical Communications, 2016, 52, 14365-14368.	4.1	37
14	Electronic Bandgap and Exciton Binding Energy of Layered Semiconductor TiS₃. Advanced Electronic Materials, 2015, 1, 1500126.	5.1	59